

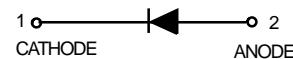
SCHOTTKY BARRIER DIODE

LBAS170HT1G
Features

- Schottky diode for high-speed switching
- Circuit protection
- Voltage clamping
- High-level detecting and mixing
- We declare that the material of product compliance with RoHS requirements.


Ordering Information

Device	Marking	Shipping
LBAS170HT1G	73	3000 Tape & Reel
LBAS170HT3G	73	10000 Tape & Reel


Maximum Ratings and Thermal Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Forward Continuous Current at $T_{amb} = 25^\circ\text{C}$	I_F	70	mA
Surge Forward Current at $t_p < 1\text{s}$, $T_{amb} = 25^\circ\text{C}$	I_{FSM}	600	mA
Power Dissipation ⁽¹⁾ at $T_{amb} = 25^\circ\text{C}$	P_{tot}	200	mW
Thermal Resistance Junction to Ambient Air ⁽¹⁾	$R_{\theta JA}$	650	$^\circ\text{C}/\text{W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Operating Temperature Range	T_{op}	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Note: (1) Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 10\mu\text{A}$ (pulsed)	70	—	—	V
Leakage Current	I_R	$V_R = 50\text{V}$ $V_R = 70\text{V}$	— —	— —	0.1 10	μA
Forward Voltage	V_F	$I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 15\text{mA}^{(1)}$	— — —	375 705 880	410 750 1000	mV
Capacitance	C_{tot}	$V_R = 0\text{V}$ $f = 1\text{MHz}$	—	1.5	2	pF
Charge Carrier Lifetime	τ	$I_F = 25\text{mA}$	—	100	—	ps
Differential Forward Resistance	R_F	$I_E = 5\text{mA}$, $f = 10\text{KHz}$	—	34	—	Ω

Note: (1) Pulse test; $t_p \leq 300\mu\text{s}$

LBAS170HT1G

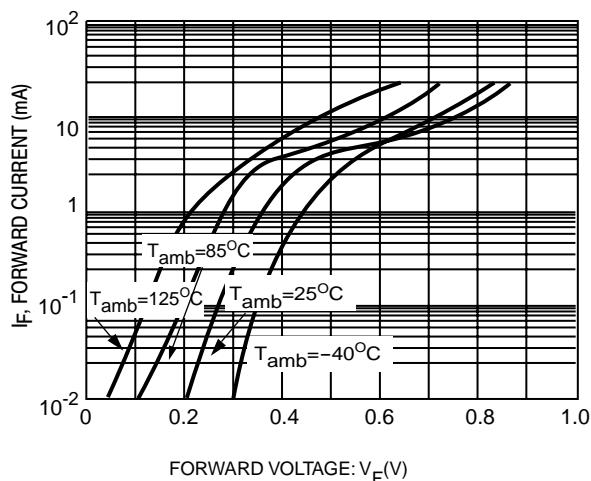
 Electrical characteristic curves($T_A = 25^\circ\text{C}$)


Fig.1 Forward current as a function of forward voltage; typical values.

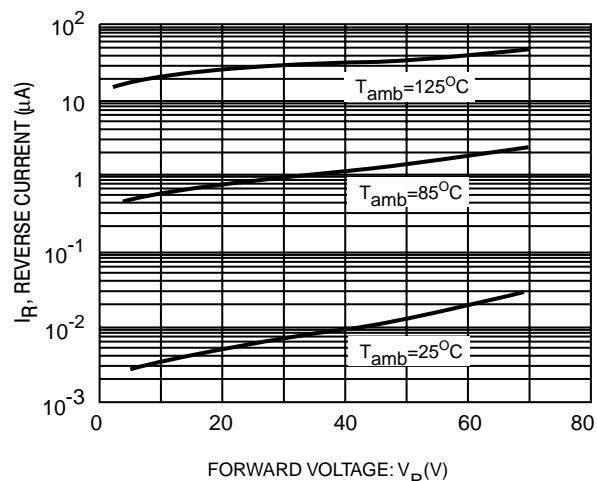


Fig.2 Reverse current as a function of reverse voltage; typical values.

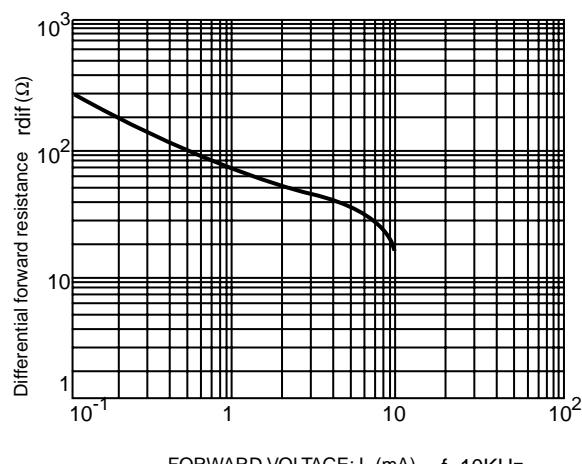


Fig.3 Differential forward resistance as a function of forward current;typical values.

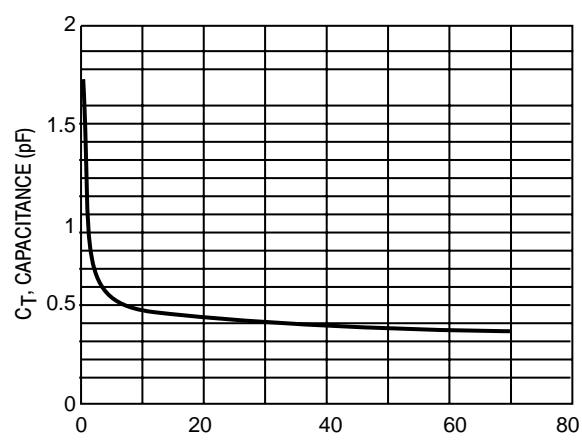
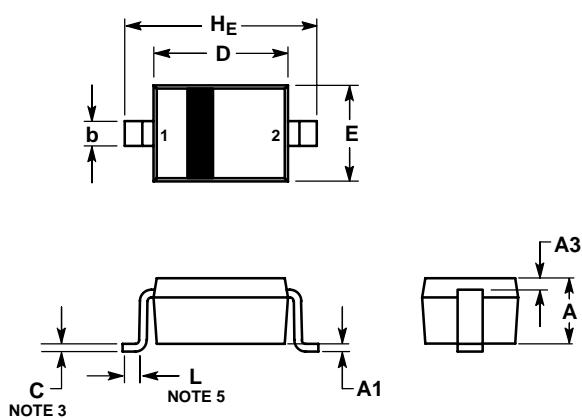


Fig.4 Diode capacitance as a function of reverse voltage;typical values.

LBAS170HT1G
SOD-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15	REF		0.006	REF	
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H _E	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*
